Midium Power Transistors (30V / 1A)

MP6X11

● Structure

NPN Silicon epitaxial planar transistor

● Features

Low saturation voltage

$V_{CE\ (sat)}$ = 0.35V (Max.) (I_C / I_B= 500mA / 25mA)

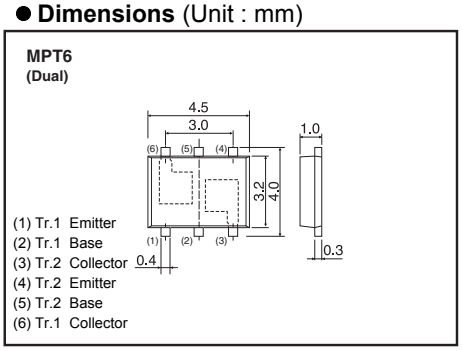
● Applications

Low Frequency Amplifier
Driver

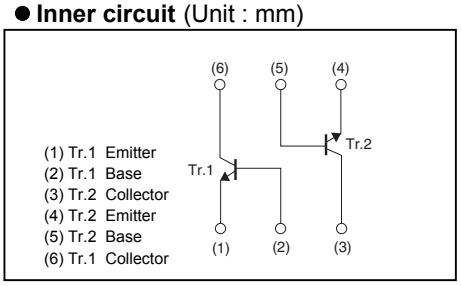
● Packaging specifications

Type	Package	MPT6
	Code	TR
	Basic ordering unit (pieces)	1000

● Dimensions (Unit : mm)



● Inner circuit (Unit : mm)



● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr.1 and Tr.2>

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	30	V
Collector-emitter voltage		V_{CEO}	30	V
Emitter-base voltage		V_{EBO}	6	V
Collector current	DC	I_C	1	A
	Pulsed	I_{CP} *1	2	A
Power dissipation		P_D *2	2.0	W/Total
		P_D *2	1.4	W/Element
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	-55 to 150	°C

*1 Pw=10ms, Single Pulse

*2 Mounted on a 40 x 40 x 0.7[mm] ceramic board.

●**Electrical characteristics** (Ta=25°C)

<It is the same characteristics for the Tr.1 and Tr.2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	30	-	-	V	I_C= 1mA
Collector-base breakdown voltage	BV_{CBO}	30	-	-	V	I_C= 10μA
Emitter-base breakdown voltage	BV_{EBO}	6	-	-	V	I_E= 10μA
Collector cut-off current	I_{CBO}	-	-	100	nV	V_{CB}= 30V
Emitter cut-off current	I_{EBO}	-	-	100	nV	V_{EB}= 6V
Collector-emitter staturation voltage	$V_{CE(sat)}$ *1	-	120	350	mV	I_C= 500mA, I_B= 25mA
DC current gain	h_{FE}	270	-	680	-	V_{CE}= 2V, I_C= 100mA
Transition frequency	f_T *1	-	320	-	MHz	V_{CE}= 2V I_E=-100mA, f=100MHz
Collector output capacitance	C_{ob}	-	7	-	pF	V_{CB}= 10V, I_E=0A f=1MHz
Turn-on time	t_{on} *2	-	90	-	ns	I_C= 500mA, I_{B1}= 25mA, I_{B2}=-25mA, V_{CC}≒5V
Storage time	t_{stg} *2	-	300	-	ns	
Fall time	t_f *2	-	60	-	ns	

*1 Pulsed

*2 See switching time test circuit

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics

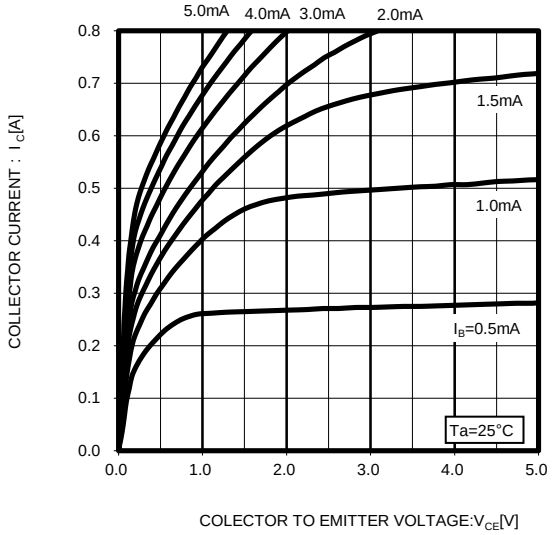


Fig.2 DC Current Gain vs. Collector Current(Ⅰ)

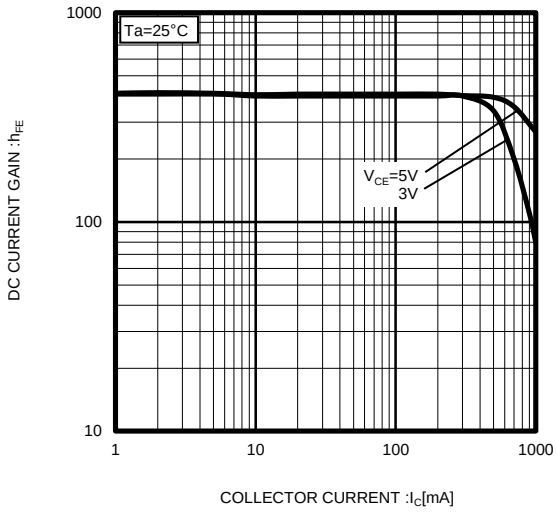


Fig.3 DC Current Gain vs. Collector Current(Ⅱ)

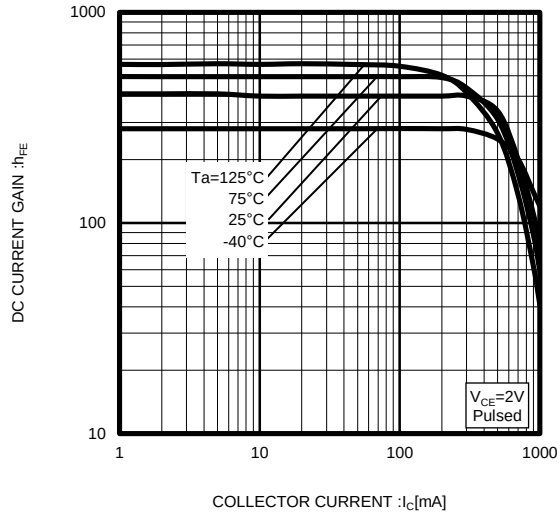


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current(Ⅰ)

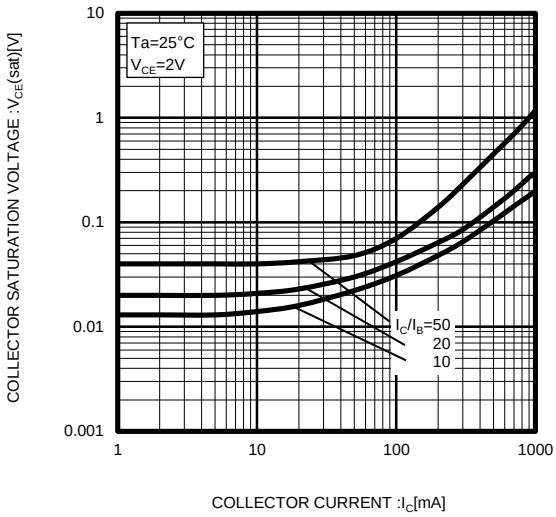


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(Ⅱ)

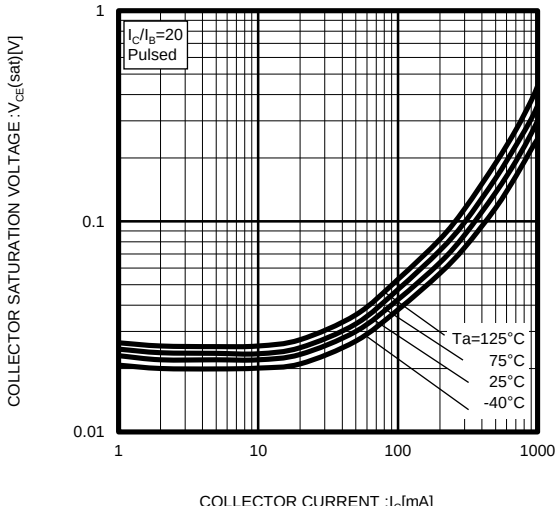


Fig.6 Ground Emitter Propagation Characteristics

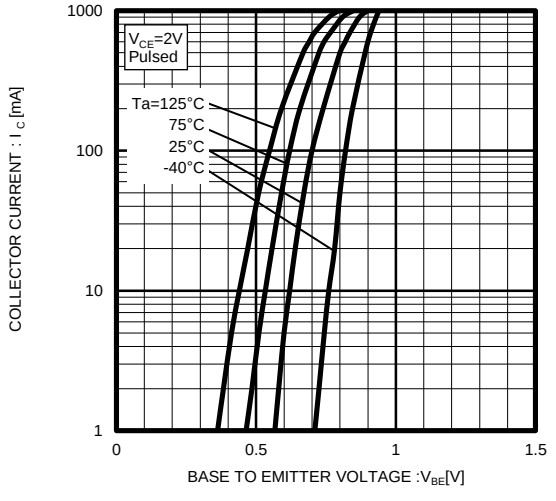


Fig.7 Emitter input capacitance vs. Emitter-Base Voltage
Collector output capacitance vs.Collector-Base Voltage

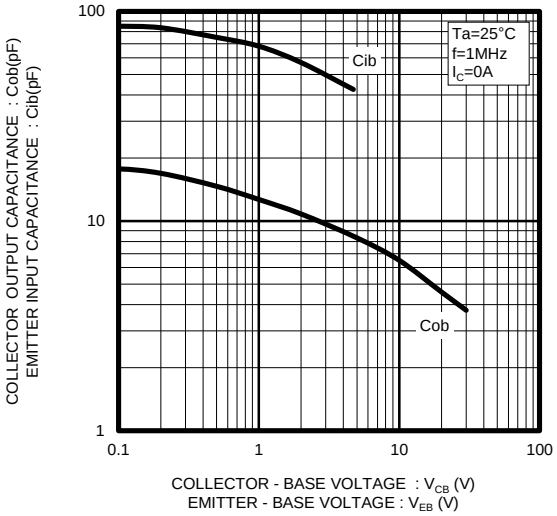


Fig8. Gain Bandwidth Product vs. Emitter Current

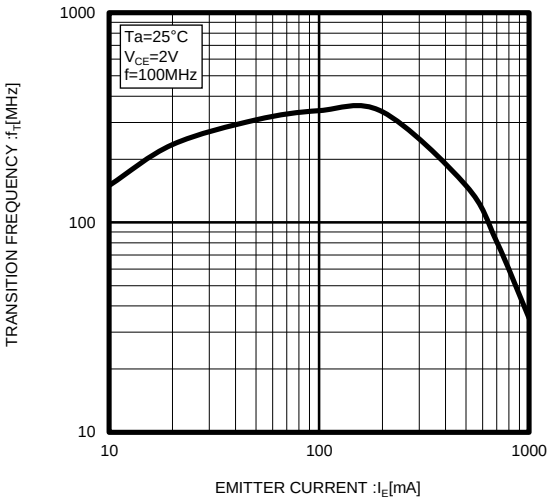
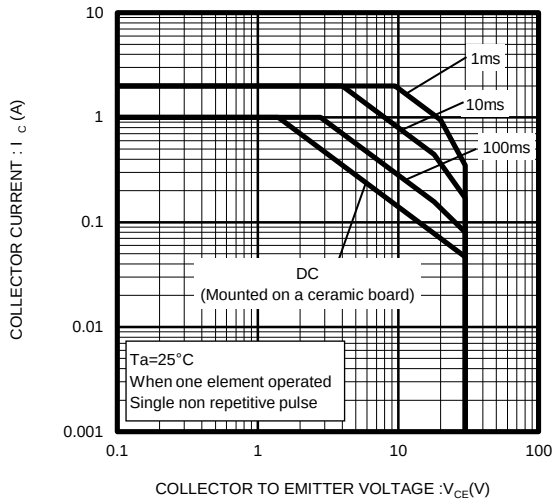
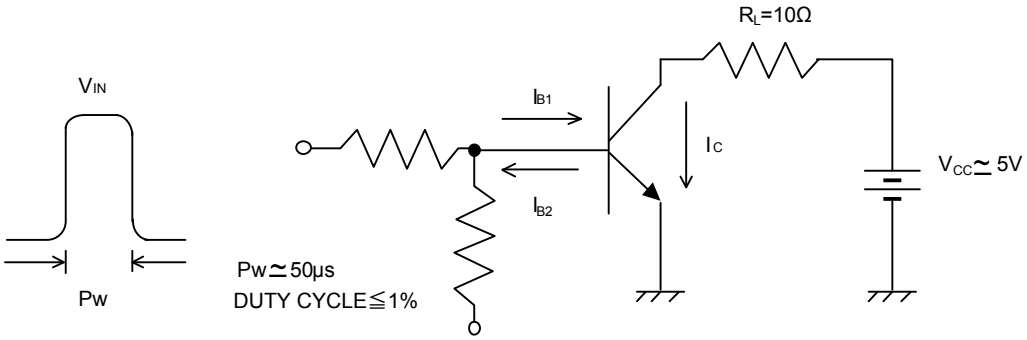


Fig9. SAFE OPERATING AREA

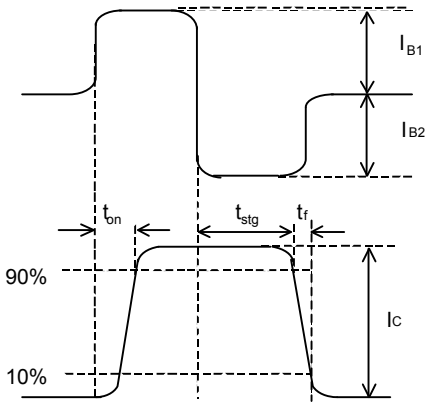


● **Switching time test circuit**



BASE CURENT WAVEFORM

COLLECTOR CURRENT WAVEFORM



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